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ABSTRACT OF THE DISCLOSURE

An input/output protection device of lateral, bipolar type quickly responds to an excess voltage pulse and/or an excess current pulse of, for example, electrostatic discharge. In a region of a first conduction type (a fourth diffusion layer) of a semiconductor substrate, a first diffusion layer of a second conduction type opposite to the first conduction type is fabricated, the layer being connected to an input/output terminal. A second diffusion layer of the second conduction type is fabricated to be connected to electrode wiring at a fixed potential. A third diffusion layer of the second conduction type is manufactured at a bottom of the second diffusion layer and is connected to the second diffusion layer. The first diffusion layer is circularly enclosed with the third diffusion layer. When a high voltage is applied to the input/output terminal, a lateral, bipolar transistor including the first diffusion layer as a collector, the second and third diffusion layers as an emitter, and the region of the first conduction type or the fourth diffusion layer as a base is put to operation.

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